US009543409B2

(12) **United States Patent**
Arvet et al.

(10) **Patent No.: US 9,543,409 B2**
(45) **Date of Patent: Jan. 10, 2017**

(54) **PRODUCTION OF SPACERS AT FLANKS OF A TRANSISTOR GATE**

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(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

(21) Appl. No.: **14/855,834**

(22) Filed: **Sep. 16, 2015**

(65) **Prior Publication Data**

US 2016/0079388 A1 Mar. 17, 2016

(30) **Foreign Application Priority Data**

Sep. 17, 2014 (FR) 14 58759

(51) **Int. Cl.**
H01L 29/66 (2006.01)
H01L 21/283 (2006.01)
(Continued)

(52) **U.S. Cl.**
CPC ***H01L 29/6656*** (2013.01); ***H01L 21/283*** (2013.01); ***H01L 21/31111*** (2013.01);
(Continued)

(58) **Field of Classification Search**
CPC H01L 29/6656; H01L 29/6653; H01L 21/823468; H01L 21/823864; H01L 21/0223; H01L 21/02247; H01L 21/0234; H01L 21/02252
See application file for complete search history.

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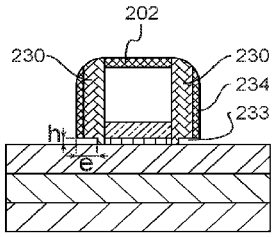
(57) **ABSTRACT**

The production of spacers at flanks of a transistor gate, including a step of forming a dielectric layer covering the gate and a peripheral region of a layer of semiconductor material surrounding the gate, including forming a superficial layer covering the gate and the peripheral region; partially removing the superficial layer configured so as to completely remove the superficial layer at the peripheral region while preserving a residual part of the superficial layer at the flanks; and selective etching of the dielectric layer vis-à-vis the material of the residual part of the superficial layer and vis-à-vis the semiconductor material.

20 Claims, 4 Drawing Sheets